



TIP102 TIP107

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP - NPN DEVICES
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

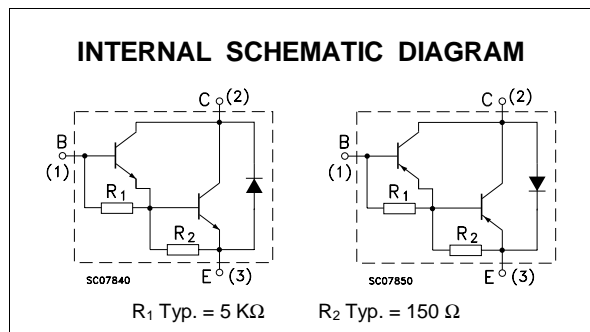
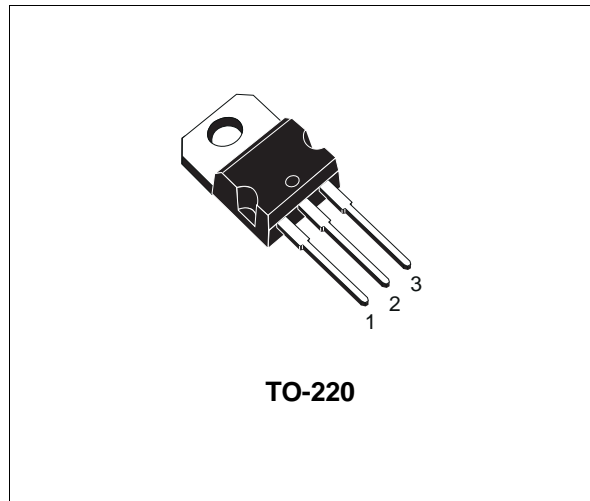
APPLICATIONS

- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT
- AUDIO POWER AMPLIFIER
- GENERAL POWER SWITCHING
- DC-AC CONVERTER
- EASY DRIVER FOR LOW VOLTAGE DC MOTOR

DESCRIPTION

The TIP102 is a silicon Epitaxial-Base NPN power transistor in monolithic Darlington configuration mounted in TO-220 plastic package. It is intended for use in power linear and switching applications.

The complementary PNP type is TIP107.



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | | Unit |
|------------------|--|-------|------------|------|
| | | NPN | TIP102 | |
| | | PNP | TIP107 | |
| V _{CBO} | Collector-Base Voltage (I _E = 0) | | 100 | V |
| V _{CEO} | Collector-Emitter Voltage (I _B = 0) | | 100 | V |
| V _{EBO} | Emitter-Base Voltage (I _C = 0) | | 5 | V |
| I _C | Collector Current | | 8 | A |
| I _{CM} | Collector Peak Current | | 15 | A |
| I _B | Base Current | | 1 | A |
| P _{tot} | Total Dissipation at T _{case} ≤ 25 °C T _{amb} ≤ 25 °C | | 80 | W |
| | | | 2 | W |
| T _{stg} | Storage Temperature | | -65 to 150 | °C |
| T _j | Max. Operating Junction Temperature | | 150 | °C |

* For PNP types voltage and current values are negative.

TIP102 / TIP107

THERMAL DATA

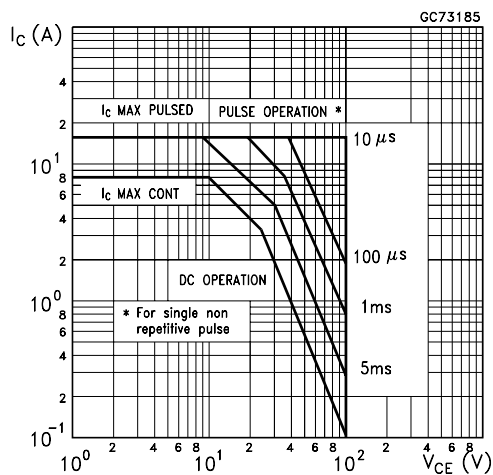
| | | | | |
|-----------------------|-------------------------------------|-----|------|------|
| R _{thj-case} | Thermal Resistance Junction-case | Max | 1.56 | °C/W |
| R _{thj-amb} | Thermal Resistance Junction-ambient | Max | 62.5 | °C/W |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------------------|---|---|-------------|------|----------|--------|
| I _{CEO} | Collector Cut-off Current (I _B = 0) | V _{CE} = 50 V | | | 50 | μA |
| I _{CBO} | Collector Cut-off Current (I _E = 0) | V _{CB} = 100 V | | | 50 | μA |
| I _{EBO} | Emitter Cut-off Current (I _C = 0) | V _{EB} = 5 V | | | 8 | mA |
| V _{CEO(sus)} * | Collector-Emitter Sustaining Voltage (I _B = 0) | I _C = 30 mA | 100 | | | V |
| V _{CE(sat)} * | Collector-Emitter Saturation Voltage | I _C = 3 A I _C = 8 A | | | 2 2.5 | V V |
| V _{BE} * | Base-Emitter Voltage | I _C = 8 A V _{CE} = 4 V | | | 2.8 | V |
| h _{FE} * | DC Current Gain | I _C = 3 A I _C = 8 A | 1000 200 | | 20000 | |
| V _F * | Forward Voltage of Commutation Diode (I _B = 0) | I _F = - I _C = 10 A | | | 2.8 | V |

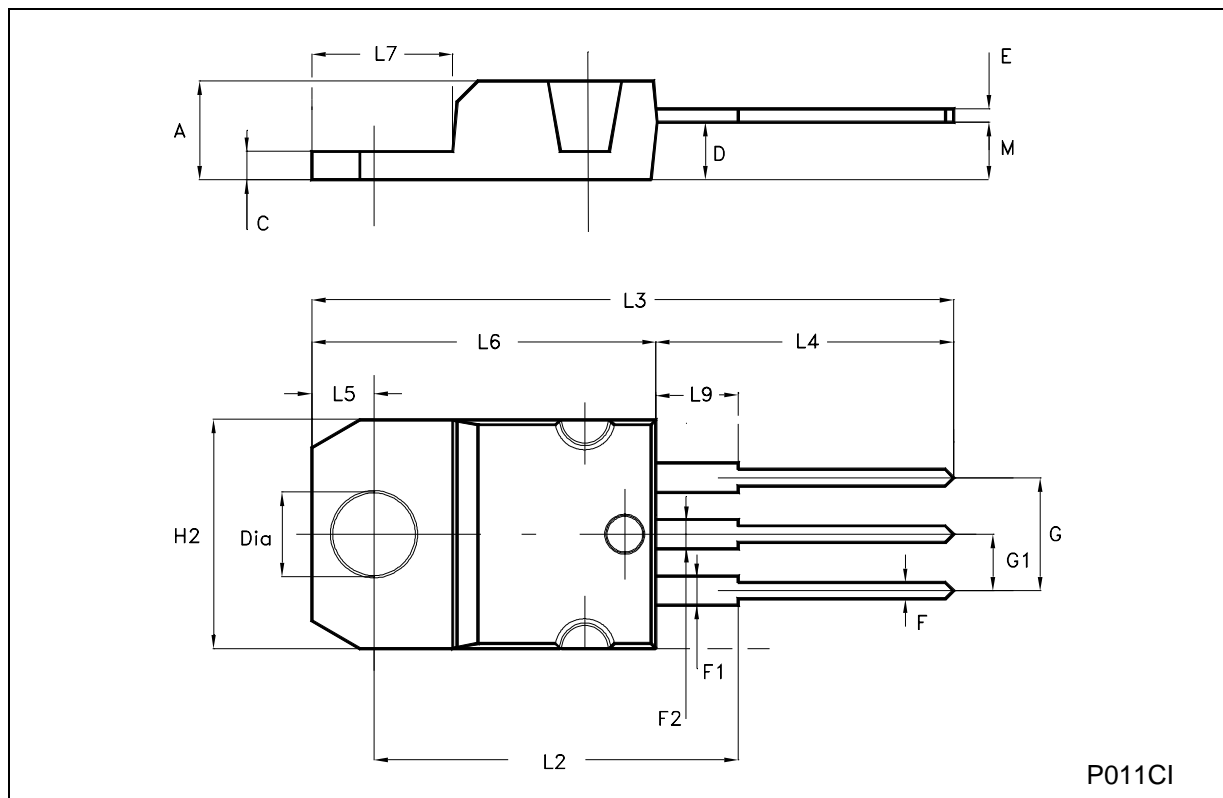
* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %
For PNP types voltage and current values are negative.

Safe Operating Area



TO-220 MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|-------|-------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| C | 1.23 | | 1.32 | 0.048 | | 0.052 |
| D | 2.40 | | 2.72 | 0.094 | | 0.107 |
| E | 0.49 | | 0.70 | 0.019 | | 0.027 |
| F | 0.61 | | 0.88 | 0.024 | | 0.034 |
| F1 | 1.14 | | 1.70 | 0.044 | | 0.067 |
| F2 | 1.14 | | 1.70 | 0.044 | | 0.067 |
| G | 4.95 | | 5.15 | 0.194 | | 0.202 |
| G1 | 2.40 | | 2.70 | 0.094 | | 0.106 |
| H2 | 10.00 | | 10.40 | 0.394 | | 0.409 |
| L2 | | 16.40 | | | 0.645 | |
| L4 | 13.00 | | 14.00 | 0.511 | | 0.551 |
| L5 | 2.65 | | 2.95 | 0.104 | | 0.116 |
| L6 | 15.25 | | 15.75 | 0.600 | | 0.620 |
| L7 | 6.20 | | 6.60 | 0.244 | | 0.260 |
| L9 | 3.50 | | 3.93 | 0.137 | | 0.154 |
| M | | 2.60 | | | 0.102 | |
| DIA. | 3.75 | | 3.85 | 0.147 | | 0.151 |



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